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November 2018

# **FQB8P10**

# P-Channel QFET® MOSFET

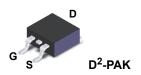
-100 V, -8.0 A, 530  $m\Omega$ 

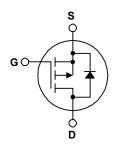
# **Description**

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- -8.0 A, -100 V,  $R_{DS(on)}$  = 530 m $\Omega$  (Max.) @  $V_{GS}$  = -10 V,  $I_{D}$  = -4.0 A
- Low Gate Charge (Typ. 12 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQB8P10TM	Unit	
$V_{DSS}$	Drain-Source Voltage		-100	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		-8.0	А	
	- Continuous (T <sub>C</sub> = 100°C)		-5.7	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-32	А	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		150	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	-8.0	А	
E <sub>AR</sub>	Repetitive Avalanche Energy (N		6.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-6.0	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *		3.75	W	
_	Power Dissipation (T <sub>C</sub> = 25°C)		65	W	
	- Derate above 25°C		0.43	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FQB8P10TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.31	
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB8P10TM	FQB8P10	D <sup>2</sup> -PAK	Tape and Reel	330 mm	24 mm	800 units

# **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-100			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 μA, Referenced to 25°C		-0.1		V/°C
I <sub>DSS</sub>	7 0 1 1/1 5 1 0 1	V <sub>DS</sub> = -100 V, V <sub>GS</sub> = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -80 V, T <sub>C</sub> = 150°C		-	-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -4.0 A		0.41	0.53	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -40 V, I <sub>D</sub> = -4.0 A		4.3		S
C <sub>iss</sub>	ic Characteristics Input Capacitance	V <sub>DS</sub> = -25 V, V <sub>GS</sub> = 0 V,		360	470	pF
C <sub>oss</sub>	Output Capacitance			120	155	рF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1.0 MHz		30	40	рF
	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			11	30	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = -50 \text{ V}, I_D = -8.0 \text{ A},$		110	230	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 25 \Omega$		20	50	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		35	80	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = -80 V, I <sub>D</sub> = -8.0 A,		12	15	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V		3.0		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		6.4		nC
	ource Diode Characteristics a	nd Maximum Ratings			I	
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-8.0	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-32	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -8.0 A			-4.0	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -8.0 A,		98		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		0.35		μС

- Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 3.5 mH, I<sub>AS</sub> = -8.0 A, V<sub>DD</sub> = -25 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub> ≤ -8.0 A, di/dt ≤ 300 A/µs , V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C .

- 4. Essentially independent of operating temperature.

# **Typical Characteristics**

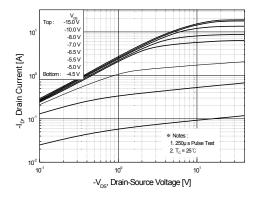


Figure 1. On-Region Characteristics

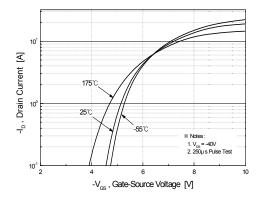


Figure 2. Transfer Characteristics

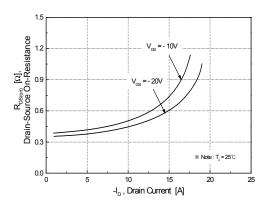


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

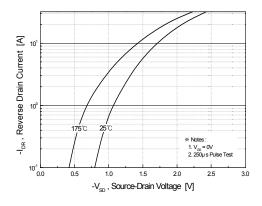


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

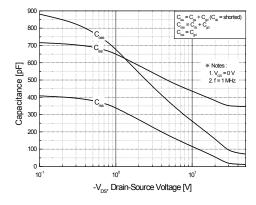


Figure 5. Capacitance Characteristics

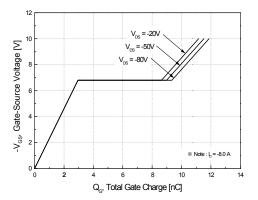


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

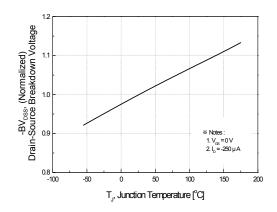
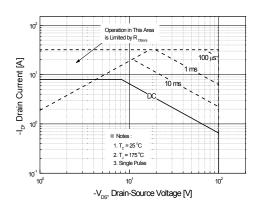


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



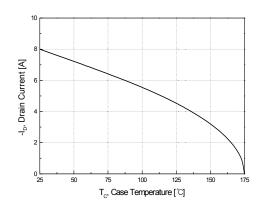


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

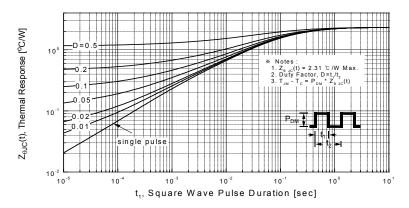


Figure 11. Transient Thermal Response Curve

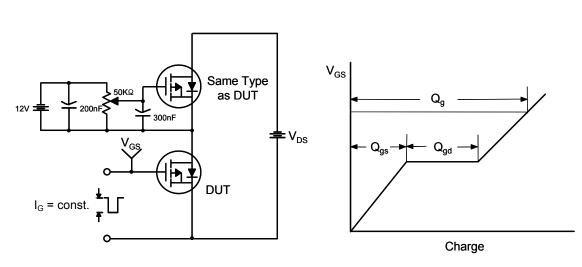


Figure 12. Gate Charge Test Circuit & Waveform

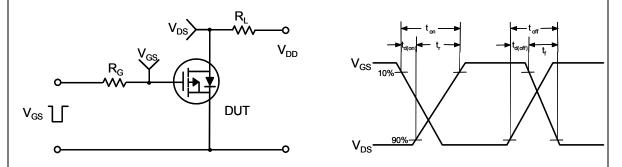


Figure 13. Resistive Switching Test Circuit & Waveforms

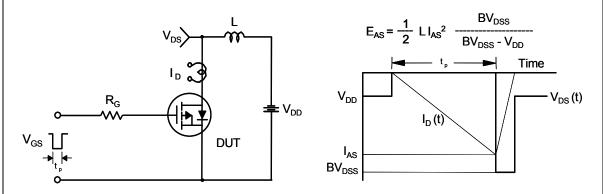
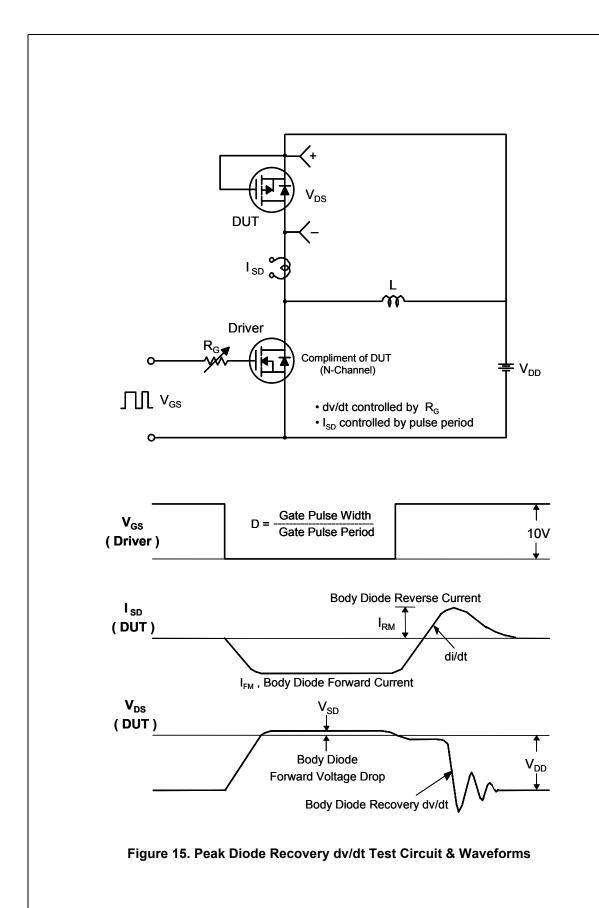


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**

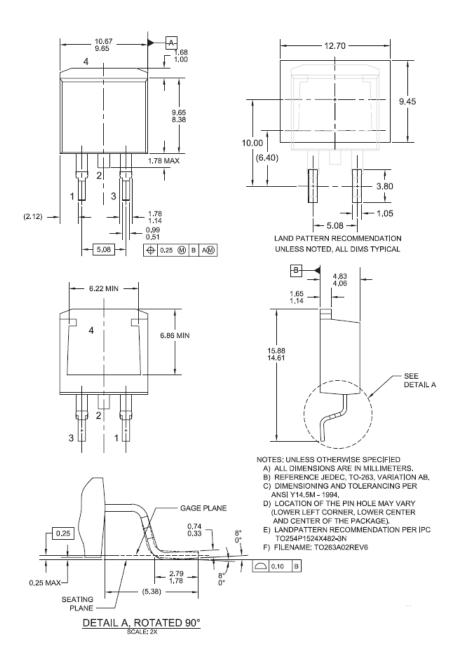


Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount

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